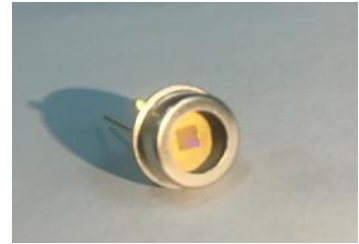




- Indium Gallium Nitride Based Material
- Photovoltaic mode operation
- TO-46 metal housing
- High responsivity and low dark current



UV LED Monitoring, UV radiation dose measurement, UV Curing

Operation temperature range	T_{opt}	-25-85	°C
Storage temperature range	T_{sto}	-40-85	°C
Soldering temperature (3 s)	T_{sol}	260	°C
Reverse voltage	V_{r-max}	-10	V
Chip size	A	1	mm ²
Dark current ($V_r = -1$ V)	I_d	<1	nA
Temperature coefficient	T_c	0.05	%/ °C
Capacitance (at 0 V and 1 MHz)	C_p	60	pF
Wavelength of peak responsivity	ρ	390	nm
Peak responsivity (at 390 nm)	R_{max}	0.289	A/W
Spectral response range ($R=0.1 \times R_{max}$)	-	290-440	nm
UV-visible rejection ratio ($R_{max}/R_{460\text{ nm}}$)	-	$>10^4$	-

